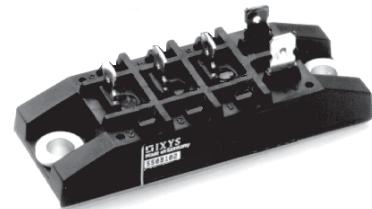
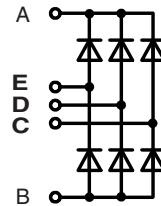


Three Phase Rectifier Bridge

I_{dAV} = 70 A
V_{RRM} = 1600 V

V _{RSM}	V _{RRM}	Types
V	V	
1700	1600	VUO 70-16NO7



Symbol	Conditions	Maximum Ratings		
I _{dAV} *	T _C = 100°C, module	70	A	
I _{FSM}	T _{VJ} = 45°C V _R = 0	550 600	A	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
	T _{VJ} = T _{VJM} V _R = 0	500 550	A	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
I ² t	T _{VJ} = 45°C V _R = 0	1520 1520	A ² s	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
	T _{VJ} = T _{VJM} V _R = 0	1250 1250	A ² s	
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine			
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+125	°C	
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	2500 3000	V~
M _d	Mounting torque (M5) (10-32 UNF)	5 ±15% 44 ±15%	Nm lb.in.	
Weight	typ.	110	g	

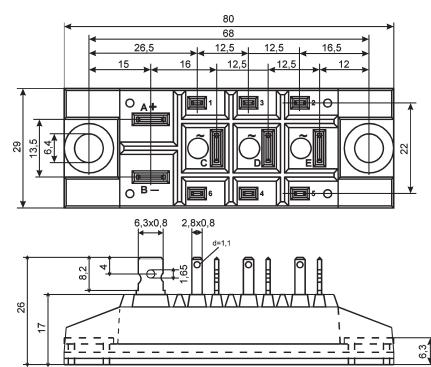
Symbol	Conditions	Characteristic Values		
I _R	V _R = V _{RRM} V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = T _{VJM}	≤ 0.5 ≤ 10	mA
V _F	I _F = 150 A	T _{VJ} = 25°C	≤ 1.7	V
V _{TO}	For power-loss calculations only		0.8 8	V mΩ
r _T				
R _{thJC}	per diode; DC current		1.45	K/W
	per module		0.242	K/W
R _{thJH}	per diode, DC current		1.9	K/W
	per module		0.317	K/W
d _s	Creeping distance on surface		16.1	mm
d _A	Creepage distance in air		7.5	mm
a	Max. allowable acceleration		50	m/s ²

Data according to IEC 60747 refer to a single diode unless otherwise stated
* for resistive load at bridge output

IXYS reserves the right to change limits, test conditions and dimensions.

© 2010 IXYS All rights reserved

Dimensions in mm (1 mm = 0.0394")



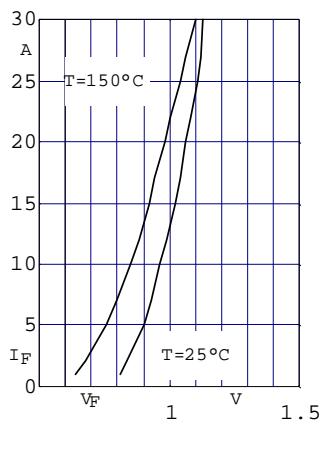


Fig. 1 Forward current versus voltage drop per diode

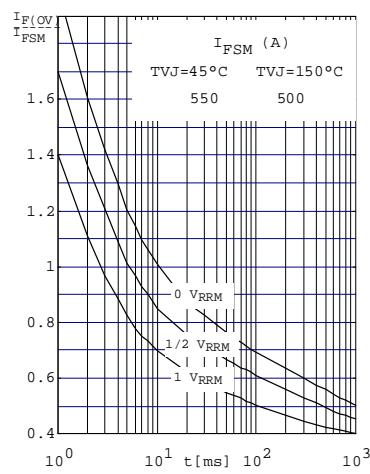


Fig. 2 Surge overload current per diode
 I_{FSM} : Crest value. t: duration

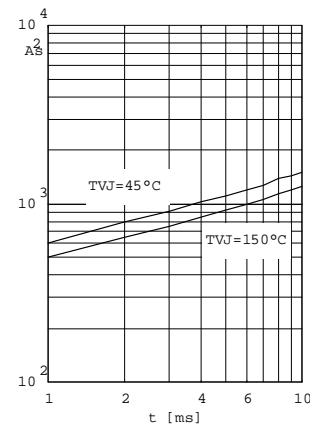


Fig. 3 I^2dt versus time (1-10ms)
per diode or thyristor

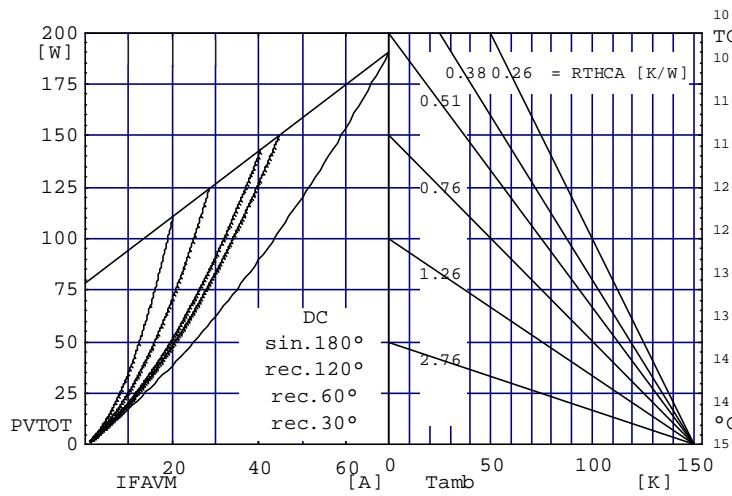


Fig. 4 Power dissipation versus direct output current and ambient temperature

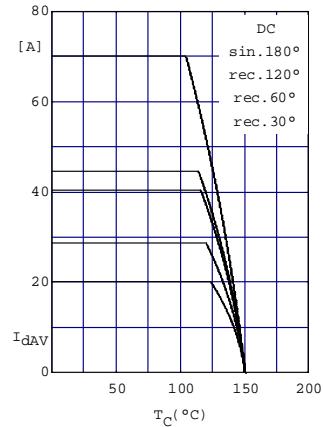


Fig. 5 Maximum forward current at case temperature

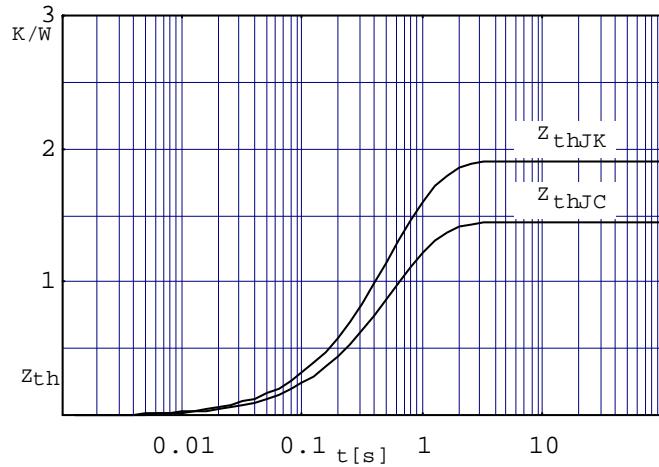


Fig. 6 Transient thermal impedance per diode/thyristor, calculated

IXYS reserves the right to change limits, test conditions and dimensions.

20100709a

© 2010 IXYS All rights reserved

2 - 2